

FMOS2304

List

List..... 1

Package outline..... 2

Features..... 2

Applications..... 2

Mechanical data..... 2

Maximum ratings 2

Electrical characteristics..... 3

Rating and characteristic curves..... 4

Pinning information..... 5

Marking..... 5

Suggested solder pad layout..... 5

Packing information..... 6

Reel packing..... 7

Suggested thermal profiles for soldering processes..... 7

FMOS2304

3.3A, 30V N-Channel Plastic-Encapsulate MOSFET

Features

- $R_{DS(ON)} \leq 60m\Omega @ V_{GS} = 10V, I_D = 3.2A.$
- $R_{DS(ON)} \leq 75m\Omega @ V_{GS} = 4.5, I_D = 2.8A.$
- We declare that the material of product compliance with RoHS requirements.
- Suffix "-H" indicates Halogen-free part, ex.FMOS2304-H.

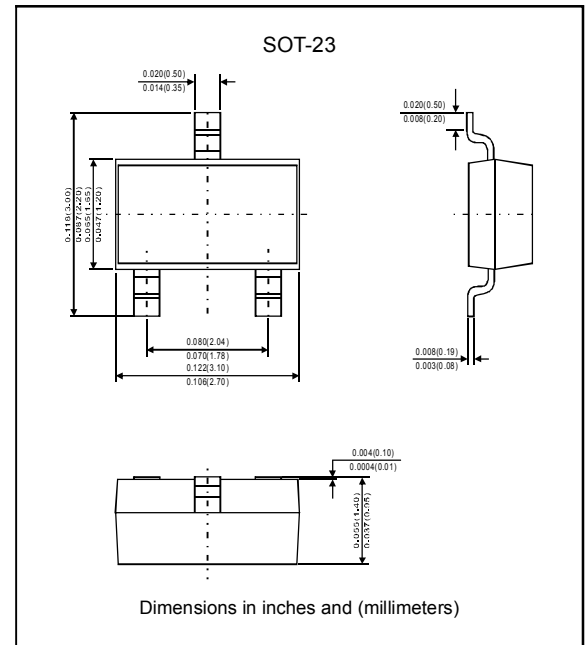
Applications

- Load switch for portable devices.
- DC / DC Converter.

Mechanical data

- Epoxy:UL94-V0 rated flame retardant.
- Case : Molded plastic, SOT-23.
- Terminals : Solder plated, solderable per MIL-STD-750, Method 2026.
- Mounting Position : Any.
- Weight : Approximated 0.008 gram.

Package outline



Maximum ratings (AT $T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Ratings	Unit
Drain-source voltage	V_{DS}	30	V
Gate-source voltage	V_{GS}	± 20	V
Continuous drain Current	I_D	3.3	A
Pulsed drain current	I_{DM}	15	A
Continuous source-drain diode current	I_S	0.9	A
Power dissipation	P_D	0.35	W
Operating Junction temperature range	T_J	+150	$^\circ C$
Storage temperature range	T_{STG}	-55 to +150	$^\circ C$
Thermal resistance Junction to ambient	$R_{\theta JA}$	357	$^\circ C/W$

FMOS2304

Electrical characteristics (At $T_A=25^\circ\text{C}$ unless otherwise noted)

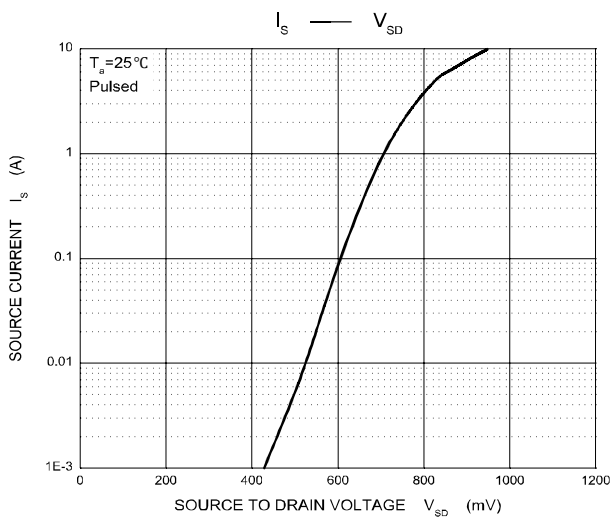
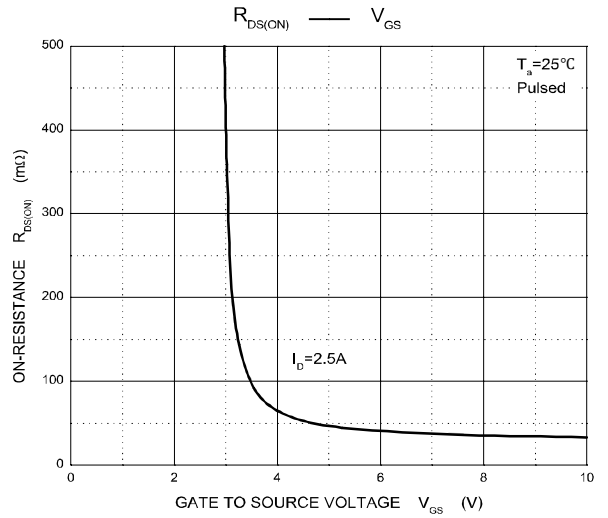
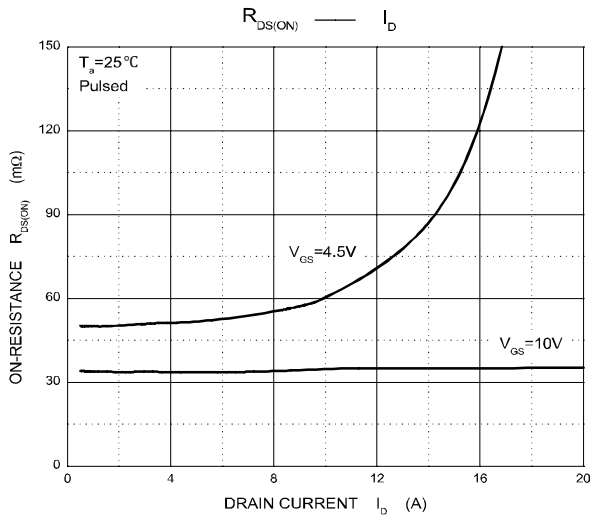
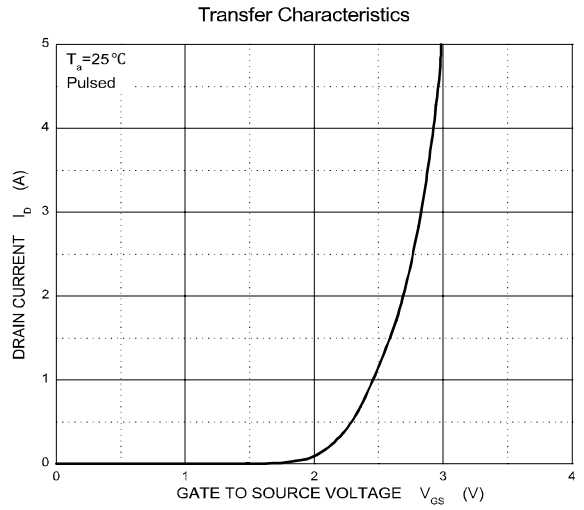
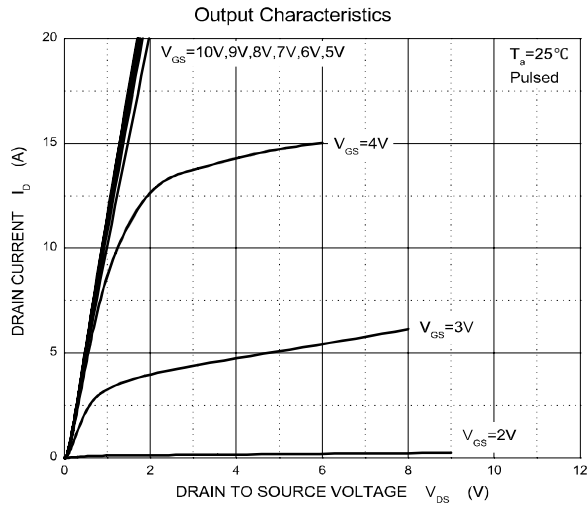
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Off characteristics						
Drain-source breakdown voltage	BV_{DSS}	$V_{GS} = 0V, I_D = 250\mu A$	30			V
Drain-source leakage current	I_{DSS}	$V_{DS} = 30V, V_{GS}=0V$			1	μA
Gate-source leakage current	I_{GSS}	$V_{GS} = \pm 20V$			± 100	nA
On characteristics						
Gate threshold voltage	$V_{GS(TH)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1.2		2.2	V
Forward trans conductance ^a	g_{FS}	$V_{DS} = 4.5V, I_D = 2.5A$	2.5			S
Static drain-source on-resistance ^a	$R_{DS(ON)}$	$V_{GS} = 10V, I_D = 3.2A$		49	60	m Ω
		$V_{GS} = 4.5V, I_D = 2.8A$		61	75	m Ω
Dynamic parameters ^b						
Input capacitance	C_{iss}	$V_{GS} = 0V, V_{DS} = 15V, f = 1.0MHz$		235		pF
Out capacitance	C_{oss}			45		
Reverse transfer capacitance	C_{rss}			17		
Switching parameters						
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 15V, V_{GS} = 4.5V, R_G = 1\Omega, R_L = 5.6\Omega, I \approx 2.7A$		12	20	ns
Rise time	t_r			50	75	
Turn-off delay time	$t_{d(off)}$			12	20	
Fall time	t_f			22	35	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 15V, V_{GS} = 10V, R_G = 1\Omega, R_L = 5.6\Omega, I \approx 2.7A$		5	10	ns
Rise time	t_r			12	20	
Turn-off delay time	$t_{d(off)}$			10	15	
Fall time	t_f			5	10	
Gate resistance	R_g	$f = 1MHz$	0.8	4.4	8.8	Ω
Total gate charge	Q_g	$V_{DS} = 15V, I_D = 3.4A, V_{GS} = 10V$		4.5	6.7	nC
Gate source charge	Q_{gs}	$V_{DS} = 15V, I_D = 3.4A, V_{GS} = 4.5V$		2.1	3.2	
Gate drain charge	Q_{gd}			0.85		
Source-drain diode ratings and characteristics						
Maximum body-diode continuous current	I_s				1.4	A
Pulse diode forward current	I_{SM}				15	A
Diode forward voltage	V_{SD}	$V_{GS} = 0V, I_s = 2.7A$		0.8	1.2	V

Notes :

a. Pulse test : Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.

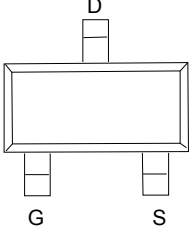
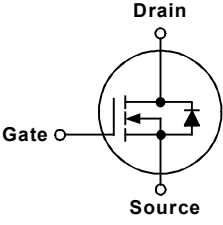
b. Guaranteed by design, not subject to production testing.

Rating and characteristic curves (FMOS2304)



FMOS2304

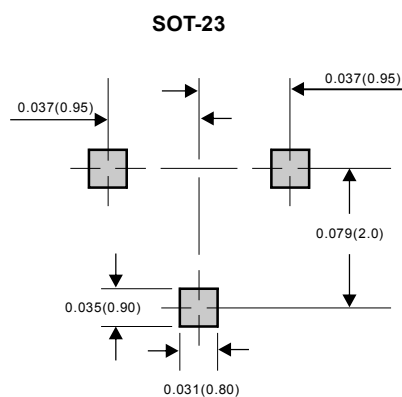
Pinning information

Pin	Simplified outline	Symbol
PinD Drain PinG Gate PinS Source		

Marking

Type number	Marking Code
FMOS2304	2304

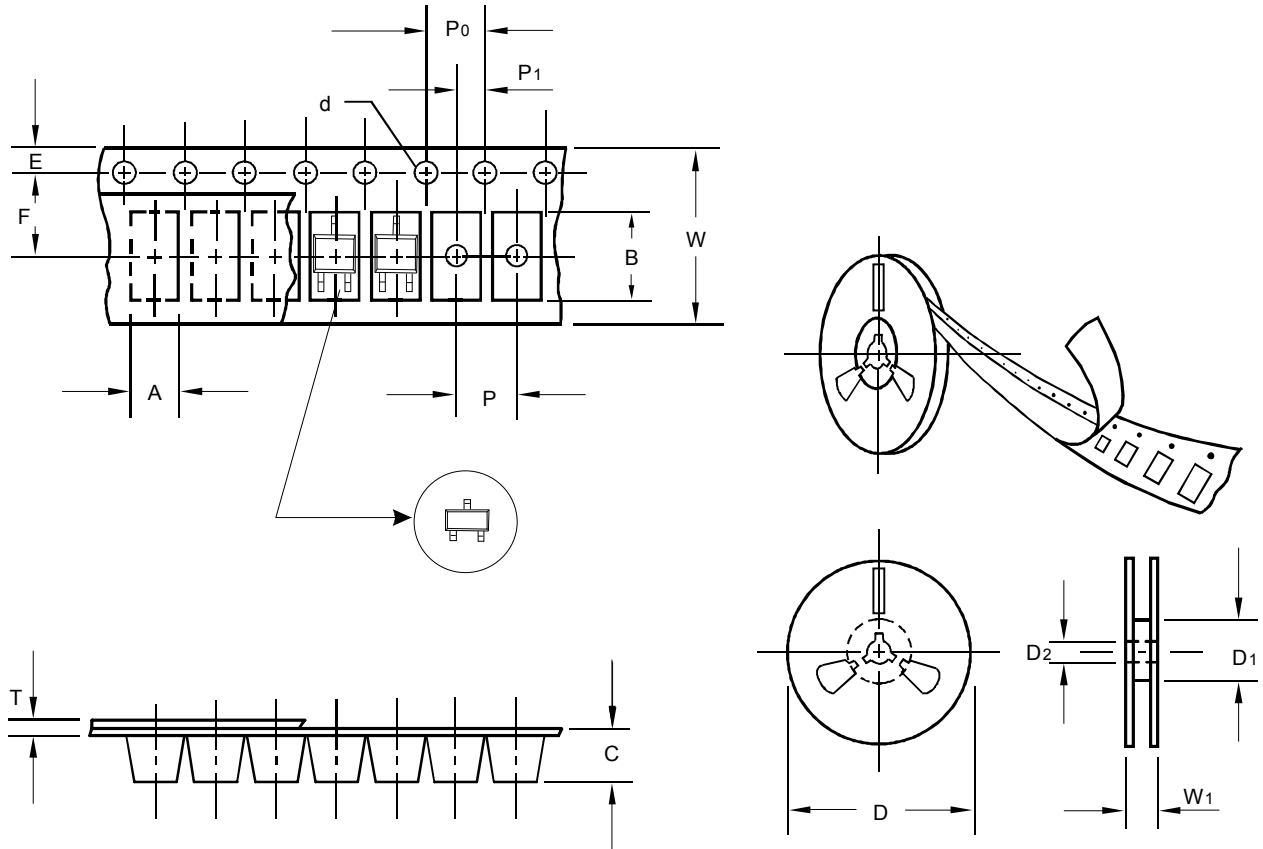
Suggested solder pad layout



Dimensions in inches and (millimeters)

FMOS2304

Packing information



unit:mm

Item	Symbol	Tolerance	SOT-23
Carrier width	A	0.1	3.15
Carrier length	B	0.1	2.77
Carrier depth	C	0.1	1.22
Sprocket hole	d	0.1	1.50
13" Reel outside diameter	D	2.0	-
13" Reel inner diameter	D1	min	-
7" Reel outside diameter	D	2.0	178.00
7" Reel inner diameter	D1	min	54.40
Feed hole diameter	D2	0.5	13.00
Sprocket hole position	E	0.1	1.75
Punch hole position	F	0.1	3.50
Punch hole pitch	P	0.1	4.00
Sprocket hole pitch	P0	0.1	4.00
Embossment center	P1	0.1	2.00
Overall tape thickness	T	0.1	0.23
Tape width	W	0.3	8.00
Reel width	W1	1.0	11.40

Note: Devices are packed in accordance with EIA standard RS-481-A and specifications listed above.

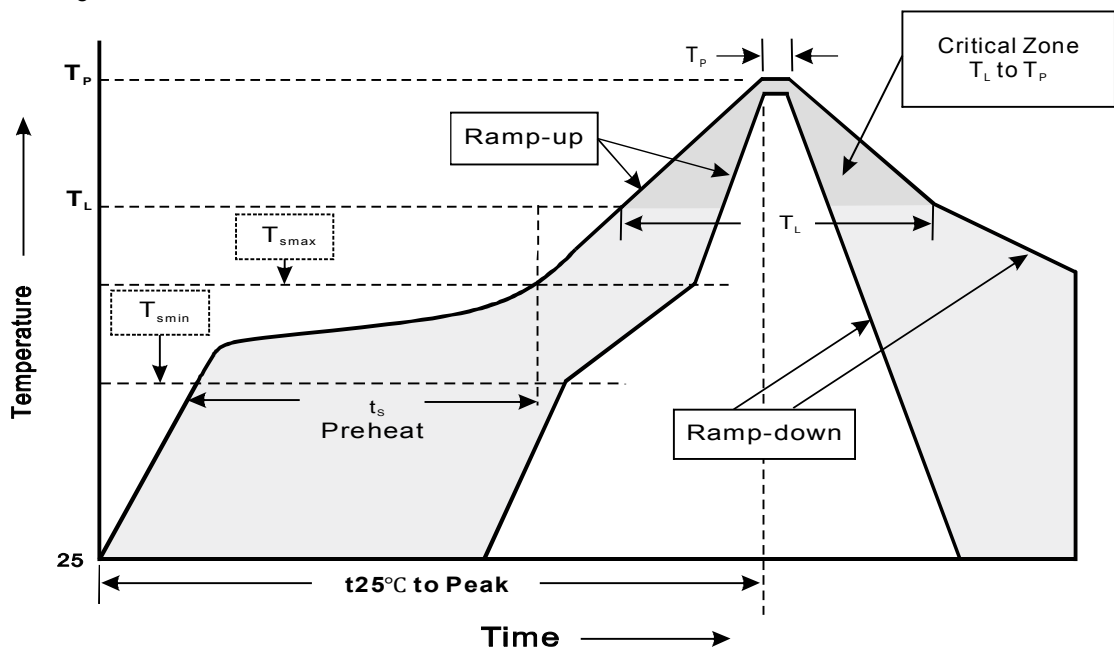
FMOS2304

Reel packing

PACKAGE	REEL SIZE	REEL (pcs)	COMPONENT SPACING (m/m)	BOX (pcs)	INNER BOX (m/m)	REEL DIA, (m/m)	CARTON SIZE (m/m)	CARTON (pcs)	APPROX. GROSS WEIGHT (kg)
SOT-23	7"	3,000	4.0	30,000	183*123*183	178	382*257*387	240,000	11.6

Suggested thermal profiles for soldering processes

- 1.Storage environment: Temperature=5°C~40°C Humidity=55%±25%
- 2.Reflow soldering of surface-mount devices



3.Reflow soldering

Profile feature	Soldering Condition
Average ramp-up rate (T_L to T_P)	< 3°C/sec
Preheat - Temperature Min (T_{smin}) - Temperature Max (T_{smax}) - Time (min to max) (t_s)	150°C 200°C 60 ~ 120sec
T_{smax} to T_L - Ramp-up rate	< 3°C/sec
Time maintained above: - Temperature (T_L) - Time(T_L)	217°C 60 ~ 260 sec
Peak Temperature(T_P)	255°C -0/+5°C
Time within 5°C of actual peak Temperature(T_P)	10 ~ 30sec
Ramp-down rate	< 6°C/sec
Time 25°C to peak temperature	< 6 minutes